

Features

- Uses PingWei advanced PerfectMOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria



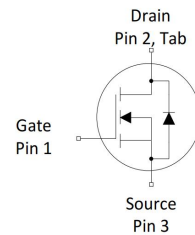
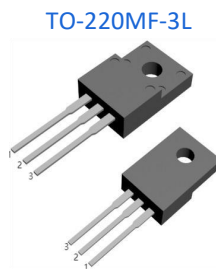
100% DVDS Tested
100% Avalanche Tested

Applications

- PFC stages, hard switching PWM stages and resonant switching
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS

Product Summary

V_{DS}	500V
$R_{DS(on)}@10V_{typ}$	220mΩ
I_D	25A



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
25N50MF	25N50MF	TO-220MF-3L	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	500	V
Continuous drain current ¹⁾ $T_C = 25^\circ C$ $T_C = 100^\circ C$	I_D	25 16	A
Pulsed drain current ($T_C = 25^\circ C$)	$I_{D \text{ pulse}}$	99	A
Avalanche energy, single pulse ($L=10mH$)	E_{AS}	500	mJ
Gate-Source voltage	V_{GS}	± 30	V
Power dissipation $T_C = 25^\circ C$	P_{tot}	130	W
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ C$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sld}	260	$^\circ C$

1) TO-220 equivalent. Limited by T_j max. $T_j = 25^\circ C$. Maximum duty cycle $D=0.5$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	1.0	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	62.5	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	500	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2	-	4	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =500V, V _{GS} =0V
		-	-	100		T _J =25°C T _J =150°C
Gate-source leakage current	I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	220	280	mΩ	V _{GS} =10V, I _D =13A
Transconductance	g _{fs}	-	29	-	S	V _{DS} =20V, I _D =13A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	3785	-	pF	V _{GS} =0V, V _{DS} =25V, f=100KHz ²⁾
Output Capacitance	C _{oss}	-	300	-		
Reverse Transfer Capacitance	C _{rss}	-	16	-		
Gate Total Charge	Q _G	-	66	-	nC	V _{DS} =250V, I _D =13A, V _{GS} =10V
Gate-Source charge	Q _{gs}	-	20	-		
Gate-Drain charge	Q _{gd}	-	16	-		
Turn-on delay time	t _{d(on)}	-	17	-	ns	V _{GS} =10V, V _{DD} =250V, R _{G_ext} =2.5Ω, I _D =6.25A
Rise time	t _r	-	16	-		
Turn-off delay time	t _{d(off)}	-	55	-		
Fall time	t _f	-	21	-		
Gate resistance	R _G	-	1.4	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.5	V	$V_{GS}=0V, I_{SD}=13A$
Body Diode Continuous Forward Current	I_S	-	-	25	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	99	A	TC = 25°C
Body Diode Reverse Recovery Time	t_{rr}	-	396	-	ns	$I_F=13A,$ $dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	4.1	-	uC	

2)100% FT tested at $V_{DS}=25V$, $f=1MHz$.

Typical Performance Characteristics

Fig 1: Output Characteristics

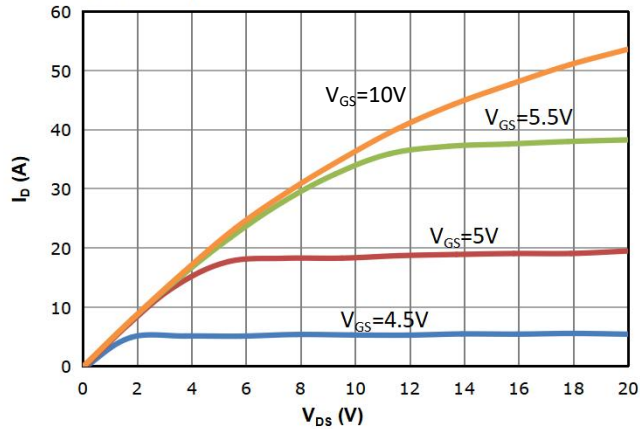


Fig 2: Transfer Characteristics

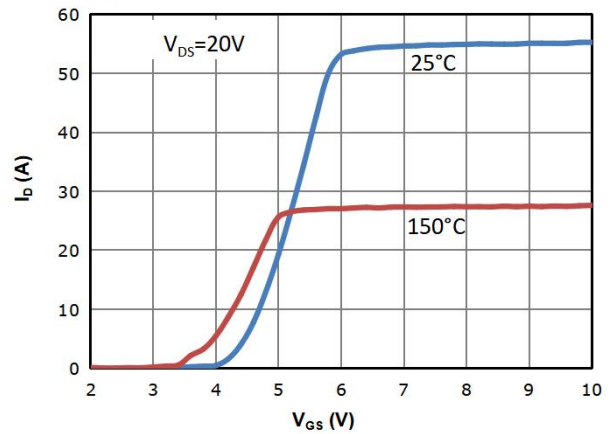


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

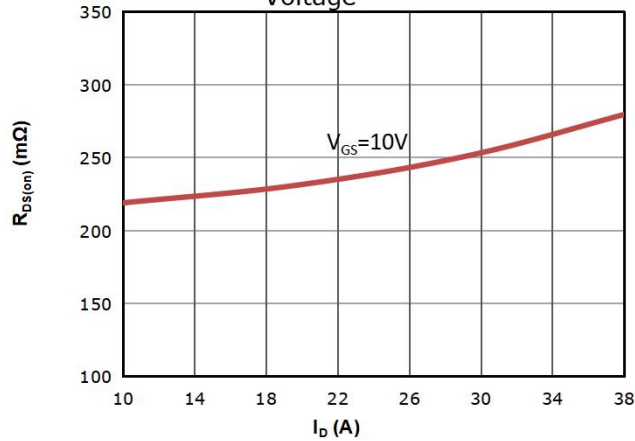


Fig 4: $R_{DS(on)}$ vs Gate Voltage

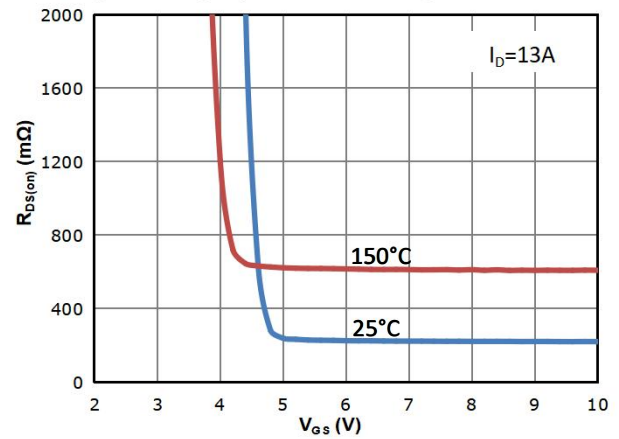


Fig 5: $R_{DS(on)}$ vs. Temperature

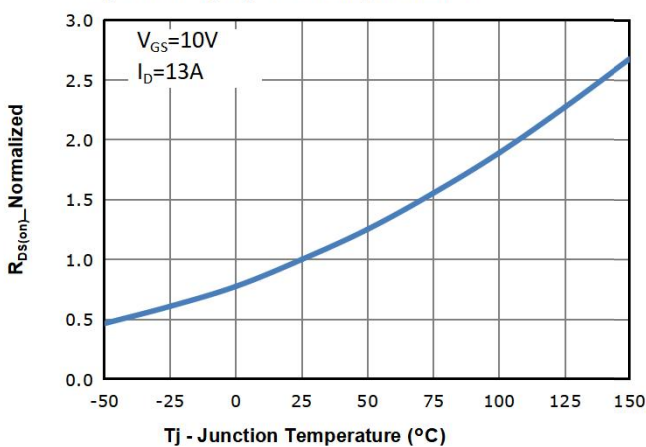


Fig 6: $V_{GS(th)}$ vs. Temperature

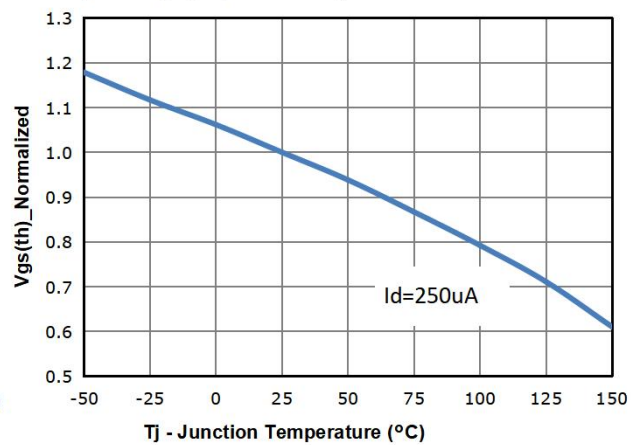


Fig 7: BVdss vs. Temperature

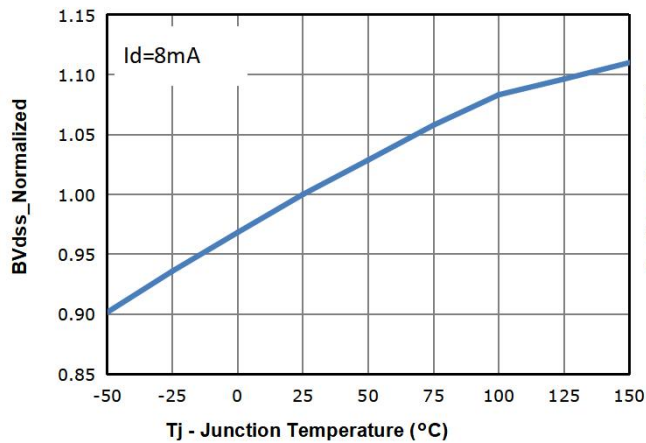


Fig 8: Capacitance Characteristics

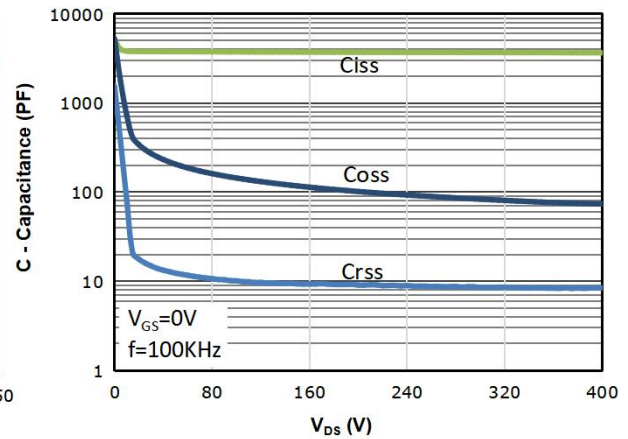


Fig 9: Gate Charge Characteristics

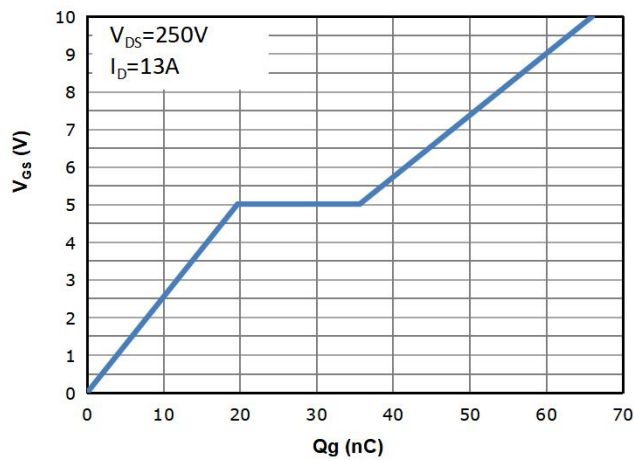


Fig 10: Body-diode Forward Characteristics

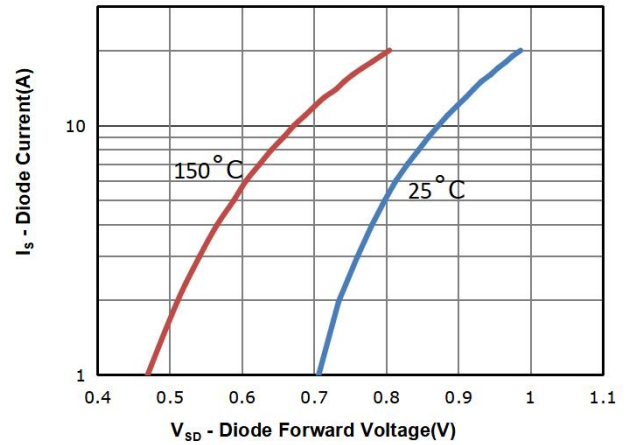


Fig 11: Power Dissipation

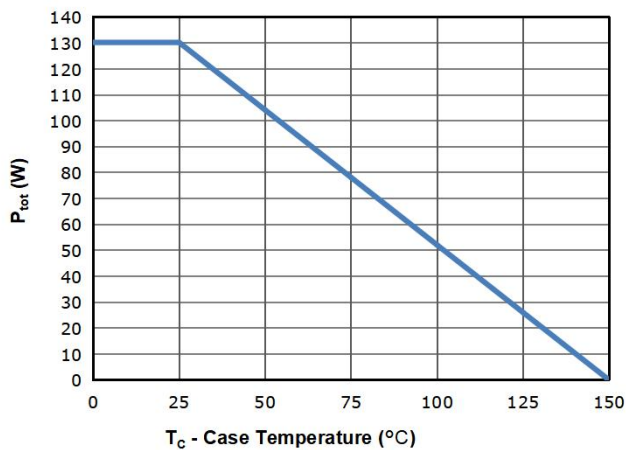


Fig 12: Drain Current Derating

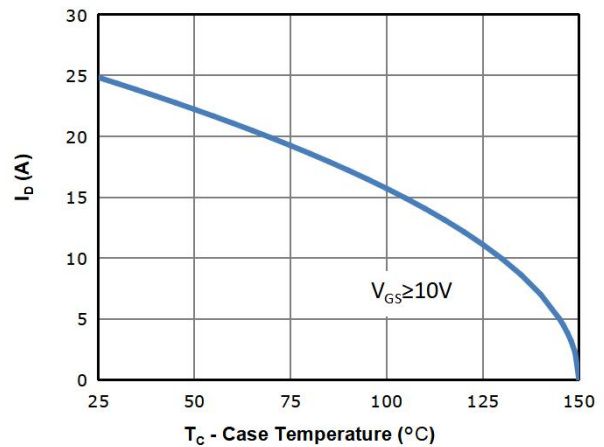


Fig 13: Safe Operating Area

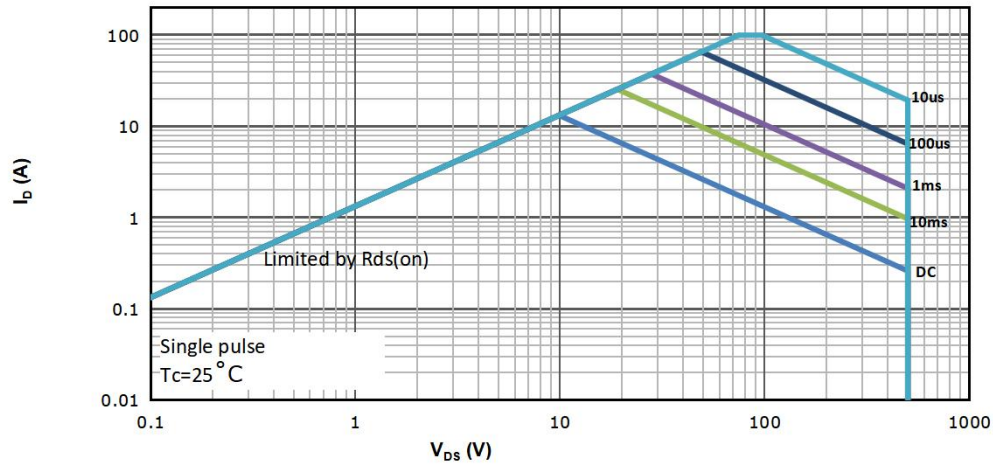
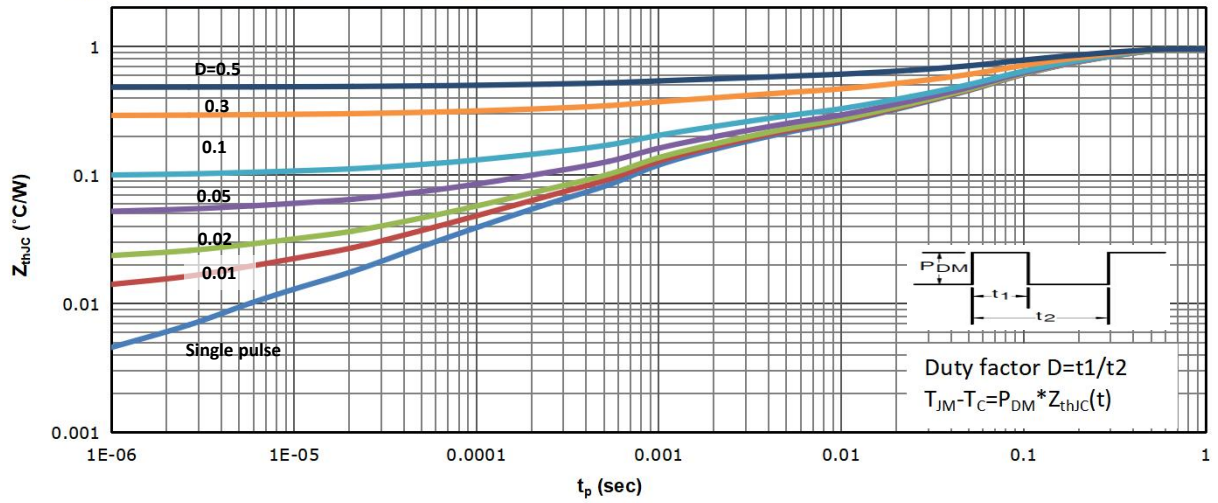
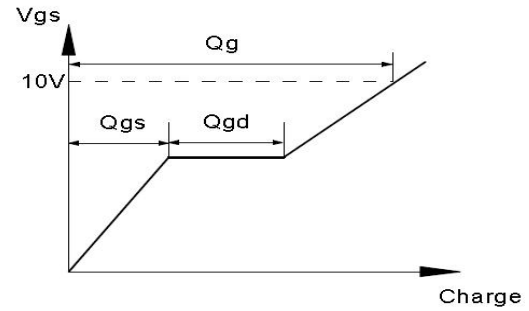
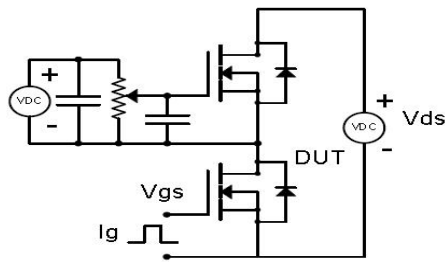


Fig 14: Max. Transient Thermal Impedance

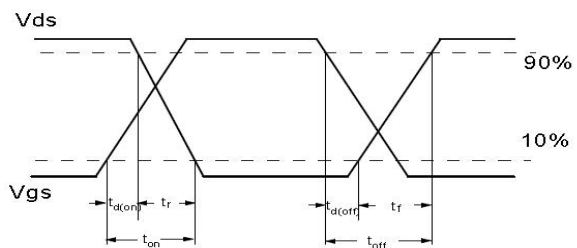
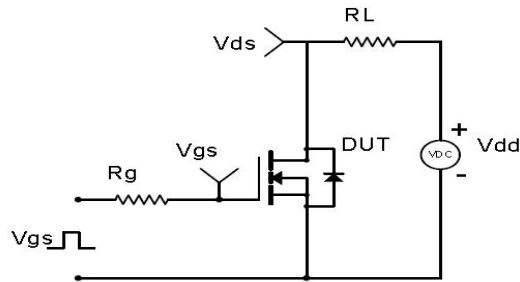


Test Circuit & Waveform

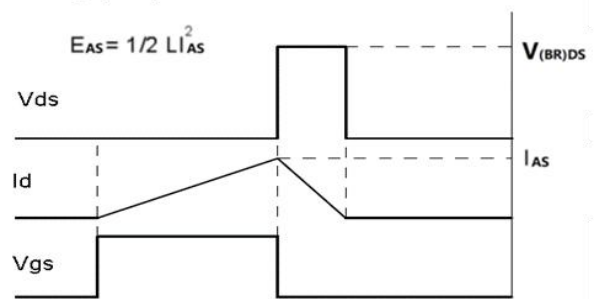
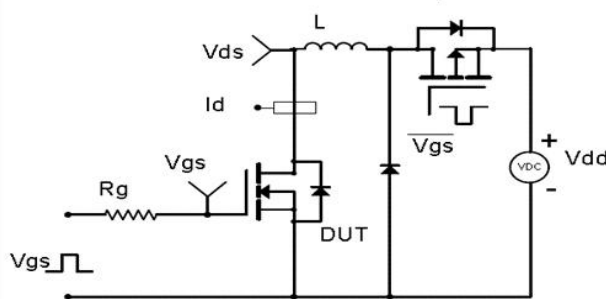
Gate Charge Test Circuit & Waveform



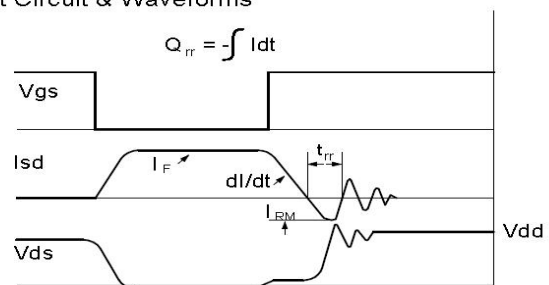
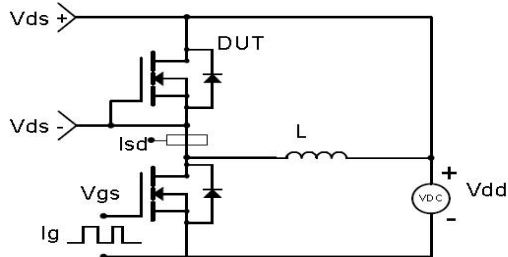
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

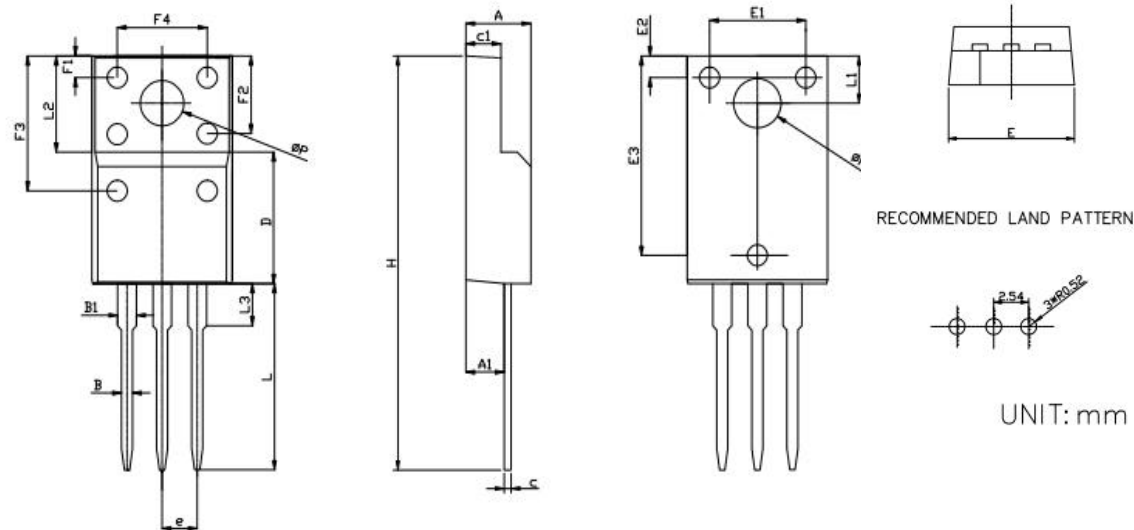


Diode Recovery Test Circuit & Waveforms





Package Outline: TO-220MF-3L



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.63	2.89	0.104	0.114
B	0.75	0.90	0.030	0.035
B1	1.15	1.55	0.045	0.061
C	0.40	0.60	0.016	0.024
C1	2.34	2.74	0.092	0.108
D	8.87	9.47	0.349	0.373
e	2.54		0.100	
E	9.86	10.46	0.388	0.412
E1	6.86	7.06	0.270	0.278
E2	1.40	1.60	0.055	
E3	13.80	14.00	0.543	0.551
F1	1.40	1.60	0.055	
F2	5.15	5.65	0.203	0.222
F3	9.10	9.70	0.358	0.382
F4	6.70	7.30	0.264	0.287
H	28.50	29.50	1.122	1.161
L	12.58	13.38	0.495	0.527
L1	3.15	3.45	0.124	0.136
L2	6.70		0.264	
L3	2.63	3.23	0.104	0.127
φP	2.90	3.48	0.114	0.137
φP1	3.15	3.75	0.124	0.148

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

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